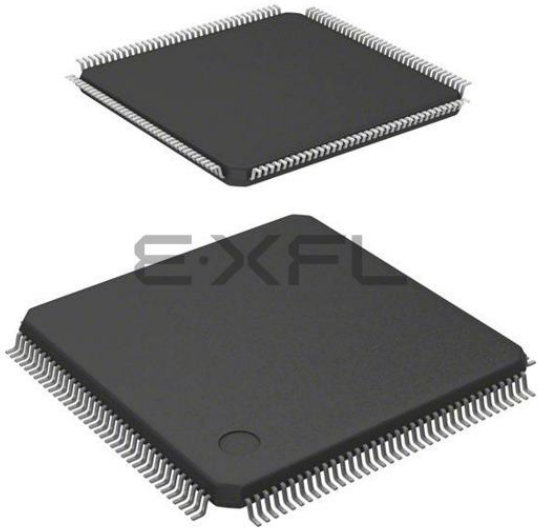

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	80
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 26x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560p54l5beaay

1 Introduction

1.1 Document overview

This document provides electrical specifications, pin assignments, and package diagrams for the SPC56xP54x/SPC56xP60x series of microcontroller units (MCUs). It also describes the device features and highlights important electrical and physical characteristics. For functional characteristics, refer to the device reference manual.

1.2 Description

This 32-bit system-on-chip (SoC) automotive microcontroller family is the latest achievement in integrated automotive application controllers. It belongs to an expanding range of automotive-focused products designed to address chassis applications specifically the airbag application.

This family is one of a series of next-generation integrated automotive microcontrollers based on the Power Architecture technology.

The advanced and cost-efficient host processor core of this automotive controller family complies with the Power Architecture embedded category. It operates up to 64 MHz and offers high performance processing optimized for low power consumption. It capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

1.3 Device comparison

Table 2 provides a summary of different members of the SPC56xP54x/SPC56xP60x family and their features—relative to Full-featured version—to enable a comparison among the family members and an understanding of the range of functionality offered within this family.

Table 2. SPC56xP54x/SPC56xP60x device comparison

Feature	SPC560P54	SPC560P60	SPC56AP54	SPC56AP60
Code Flash memory (with ECC)	768 KB	1 MB	768 KB	1 MB
Data Flash / EE (with ECC)	64 KB			
SRAM (with ECC)	64 KB	80 KB	64 KB	80 KB
Processor core	32-bit e200z0h		32-bit Dual e200z0h	
Instruction set	VLE			
CPU performance	0-64 MHz			
FMPLL (frequency-modulated phase-locked loop) modules	1			
INTC (interrupt controller) channels	148			
PIT (periodic interrupt timer)	1 (includes four 32-bit timers)			

SPC56xP54x/SPC56xP60x is present on the market in two different options enabling different features: Full-featured, and Airbag configuration. *Table 3* shows the main differences between the two versions.

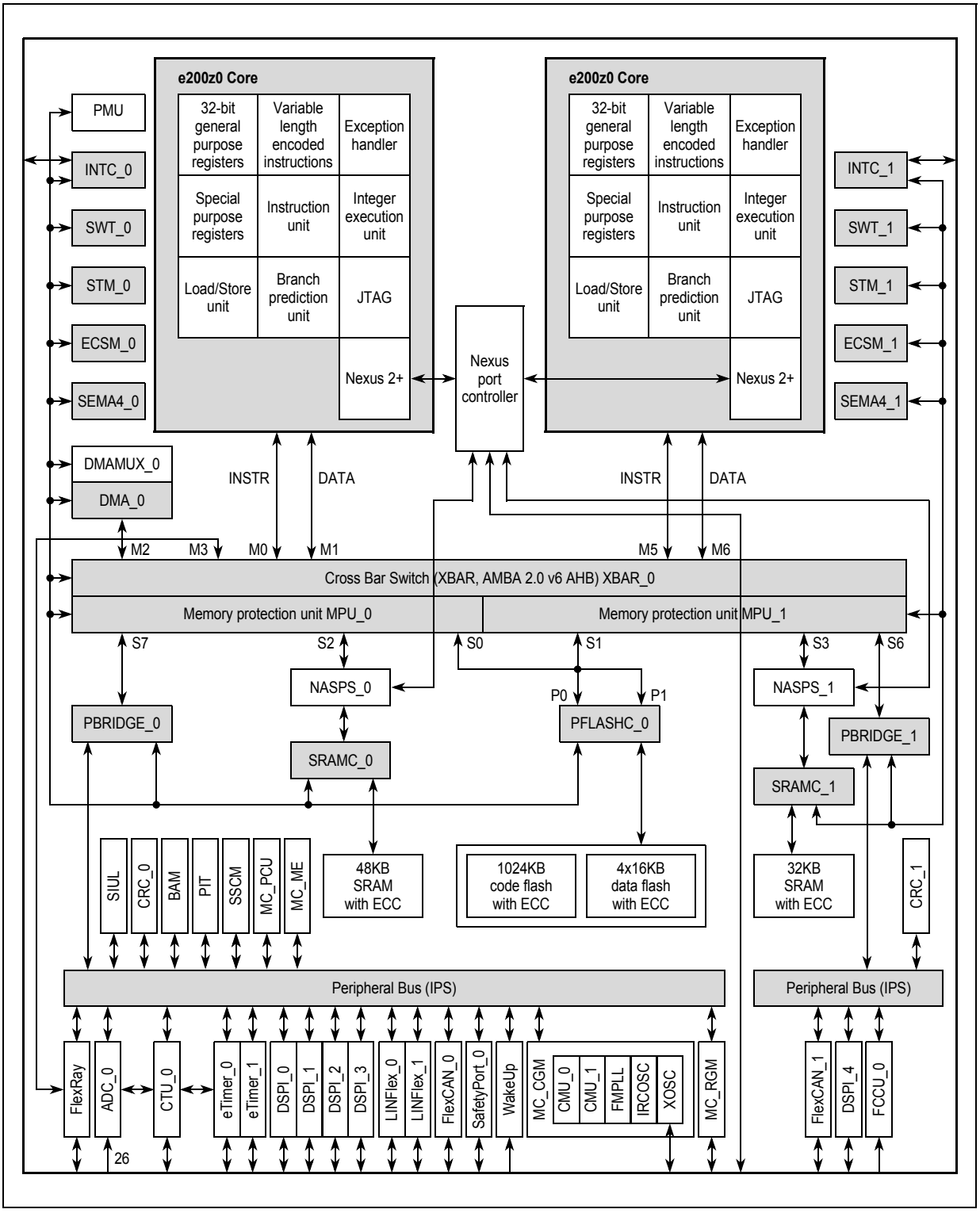
Table 3. SPC56xP54x/SPC56xP60x device configuration difference

Feature	Enhanced Full-featured	Full-featured	Airbag
FlexCAN (controller area network)	3	2	2
CTU (cross triggering unit)	Yes		No
FlexRay	Yes (64 message buffer)		No
DSPI (deserial serial peripheral interface) modules	5		4
CRC (cyclic redundancy check) unit	2		1

1.4 Block diagram

Figure 1 shows a top-level block diagram of the SPC56xP54x/SPC56xP60x MCU. *Table 4* summarizes the functions of the blocks.

Figure 1. SPC56xP54x/SPC56xP60x block diagram

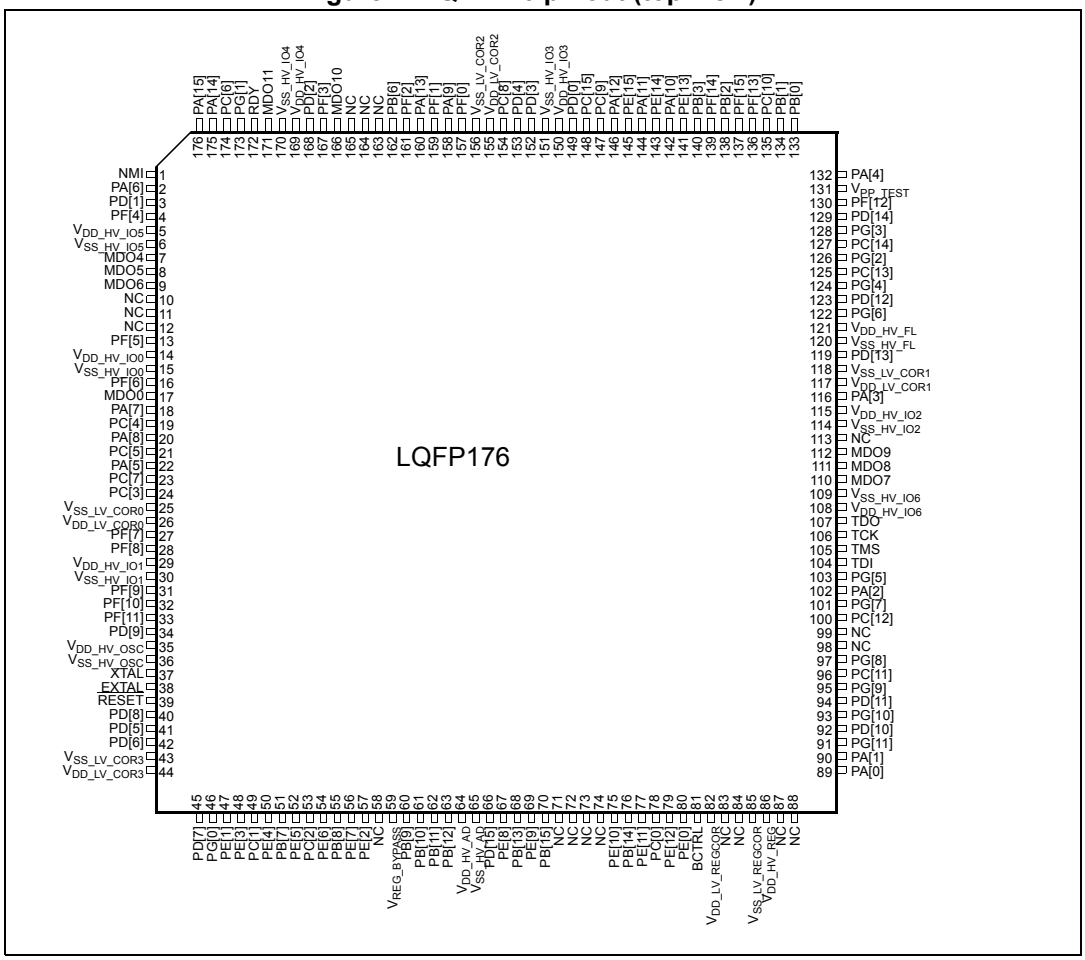


2 Package pinouts and signal descriptions

2.1 Package pinouts

The LQFP pinouts are shown in the following figures.

Figure 2. LQFP176 pinout (top view)[b]



b. Software development package only. Not available for production.

Table 7. Pin muxing[1] (continued)

Port pin	PCR No.	Alternate function[2], [3]	Functions	Peripheral [4]	I/O direction [5]	Pad speed[6]		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176[7]
Port B										
B[0]	PCR[16]	ALT0 ALT1 ALT2 ALT3 —	GPIO[16] TXD ETC[2] DEBUG[0] EIRQ[15]	SIUL FlexCAN_0 eTimer_1 SSCM SIUL	I/O O I/O — I	Slow	Medium	76	109	133
B[1]	PCR[17]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[17] CS7_1 ETC[3] DEBUG[1] RXD EIRQ[16]	SIUL DSPI_1 eTimer_1 SSCM FlexCAN_0 SIUL	I/O O I/O — I I	Slow	Medium	77	110	134
B[2]	PCR[18]	ALT0 ALT1 ALT2 ALT3 —	GPIO[18] TXD SOUT_4 DEBUG[2] EIRQ[17]	SIUL LINFlex_0 DSPI_4 SSCM SIUL	I/O O I/O — I	Slow	Medium	79	114	138
B[3]	PCR[19]	ALT0 ALT1 ALT2 ALT3 —	GPIO[19] — SCK_4 DEBUG[3] RXD	SIUL — DSPI_4 SSCM LINFlex_0	I/O — I/O — I	Slow	Medium	80	116	140
B[6]	PCR[22]	ALT0 ALT1 ALT2 ALT3 —	GPIO[22] clk_out CS2_2 clk_out_div256 EIRQ[18]	SIUL MC_CGL DSPI_2 MC_CGL SIUL	I/O O O O I	Slow	Medium	96	138	162
B[7]	PCR[23]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[23] — — — AN[0] RXD	SIUL — — — ADC_0 LINFlex_0	Input Only	—	—	29	43	51
B[8]	PCR[24]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[24] — — — AN[1] ETC[5]	SIUL — — — ADC_0 eTimer_0	Input Only	—	—	31	47	55

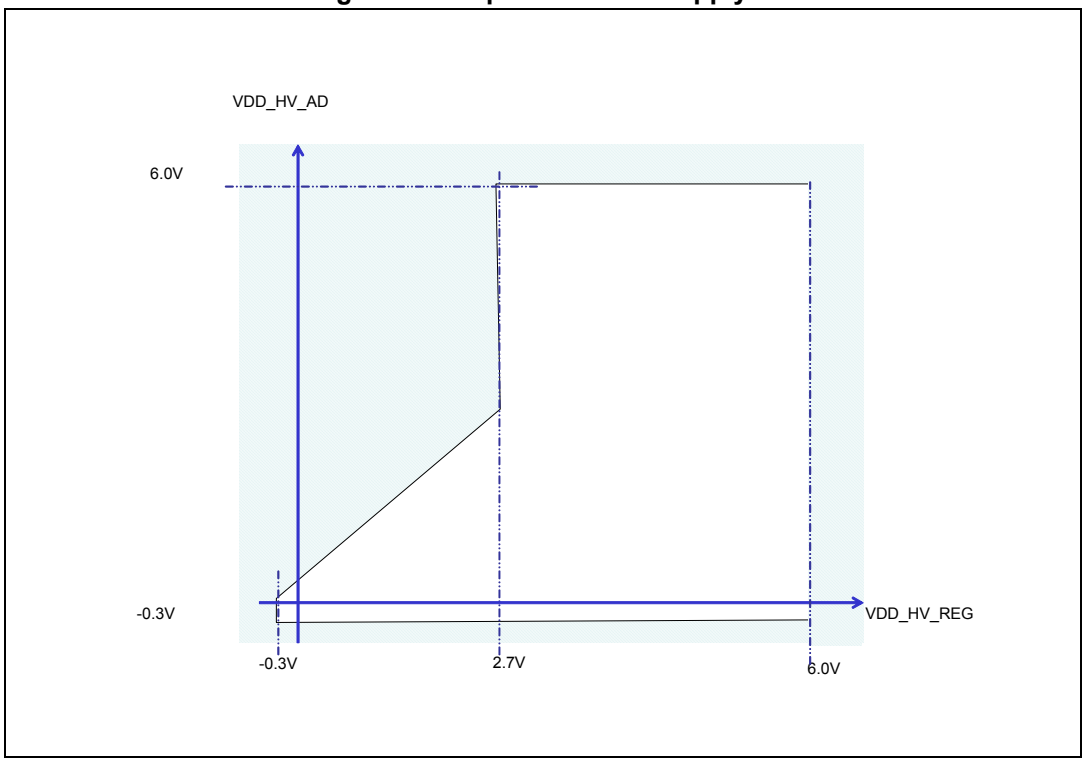
Table 7. Pin muxing[1] (continued)

Port pin	PCR No.	Alternate function[2], [3]	Functions	Peripheral [4]	I/O direction [5]	Pad speed[6]		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176[7]
Port C										
C[0]	PCR[32]	ALT0 ALT1 ALT2 ALT3 —	GPIO[32] — — — AN[19]	SIUL — — — ADC_0	Input Only	—	—	45	66	78
C[1]	PCR[33]	ALT0 ALT1 ALT2 ALT3 —	GPIO[33] — — — AN[2]	SIUL — — — ADC_0	Input Only	—	—	28	41	49
C[2]	PCR[34]	ALT0 ALT1 ALT2 ALT3 —	GPIO[34] — — — AN[3]	SIUL — — — ADC_0	Input Only	—	—	30	45	53
C[3]	PCR[35]	ALT0 ALT1 ALT2 ALT3 —	GPIO[35] CS1_0 ETC[4] TXD EIRQ[21]	SIUL DSPI_0 eTimer_1 LINFlex_1 SIUL	I/O O I/O O I	Slow	Medium	10	16	24
C[4]	PCR[36]	ALT0 ALT1 ALT2 ALT3 —	GPIO[36] CS0_0 — DEBUG[4] EIRQ[22]	SIUL DSPI_0 — SSCM SIUL	I/O I/O — — I	Slow	Medium	5	11	19
C[5]	PCR[37]	ALT0 ALT1 ALT2 ALT3 —	GPIO[37] SCK_0 SCK_4 DEBUG[5] EIRQ[23]	SIUL DSPI_0 DSPI_4 SSCM SIUL	I/O I/O I/O — I	Slow	Medium	7	13	21
C[6]	PCR[38]	ALT0 ALT1 ALT2 ALT3 —	GPIO[38] SOUT_0 — DEBUG[6] EIRQ[24]	SIUL DSPI_0 — SSCM SIUL	I/O O — — I	Slow	Medium	98	142	174

Table 7. Pin muxing[1] (continued)

Port pin	PCR No.	Alternate function[2], [3]	Functions	Peripheral [4]	I/O direction [5]	Pad speed[6]		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176[7]
Port G										
G[0]	PCR[96]	ALT0 ALT1 ALT2 ALT3 —	GPIO[96] F[0] — — EIRQ[30]	SIUL FCCU — — SIUL	I/O O — — I	Slow	Medium	—	38	46
G[1]	PCR[97]	ALT0 ALT1 ALT2 ALT3 —	GPIO[97] F[1] — — EIRQ[31]	SIUL FCCU — — SIUL	I/O O — — I	Slow	Medium	—	141	173
G[2]	PCR[98]	ALT0 ALT1 ALT2 ALT3 —	GPIO[98] — — — SIN_4	SIUL — — — DSPI_4	I/O — — — I	Slow	Medium	—	102	126
G[3]	PCR[99]	ALT0 ALT1 ALT2 ALT3	GPIO[99] — SOUT_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	104	128
G[4]	PCR[100]	ALT0 ALT1 ALT2 ALT3	GPIO[100] — SCK_4 —	SIUL — DSPI_4 —	I/O — I/O —	Slow	Medium	—	100	124
G[5]	PCR[101]	ALT0 ALT1 ALT2 ALT3	GPIO[101] — CS0_4 —	SIUL — DSPI_4 —	I/O — I/O —	Slow	Medium	—	85	103
G[6]	PCR[102]	ALT0 ALT1 ALT2 ALT3	GPIO[102] — CS1_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	98	122
G[7]	PCR[103]	ALT0 ALT1 ALT2 ALT3	GPIO[103] — CS2_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	83	101

Figure 6. Independent ADC supply[e]



3.4 Recommended operating conditions

Table 10. Recommended operating conditions (5.0 V)

Symbol		Parameter	Conditions	Min	Max[1]	Unit
V_{SS_HV}	SR	Digital ground	—	0	0	V
$V_{DD\_HV\_IOx}$[2]	SR	5.0 V input/output supply voltage	—	4.5	5.5	V
$V_{SS\_HV\_IOx}$	SR	Input/output ground voltage	—	0	0	V
$V_{DD\_HV\_FL}$	SR	5.0 V code and data flash memory supply voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_IOx}$	$V_{DD\_HV\_IOx}$ – 0.1	$V_{DD\_HV\_IOx}$ + 0.1	
$V_{SS\_HV\_FL}$	SR	Code and data flash memory ground	—	0	0	V
$V_{DD\_HV\_OSC}$	SR	5.0 V crystal oscillator amplifier supply voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_IOx}$	$V_{DD\_HV\_IOx}$ – 0.1	$V_{DD\_HV\_IOx}$ + 0.1	
$V_{SS\_HV\_OSC}$	SR	5.0 V crystal oscillator amplifier reference voltage	—	0	0	V

e. Device design targets the removal of this conditions. To be confirmed by design during device validation.

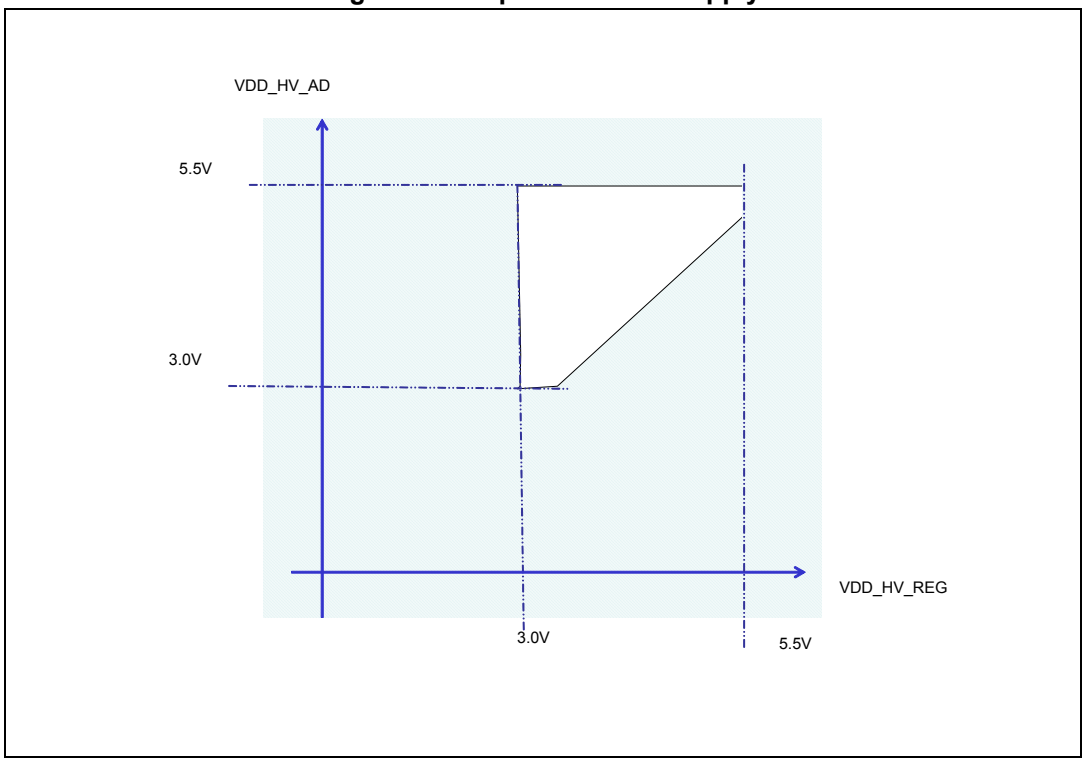
Table 11. Recommended operating conditions (3.3 V) (continued)

Symbol		Parameter	Conditions	Min	Max(1)	Unit
$V_{DD\_HV\_REG}$	SR	3.3 V voltage regulator supply voltage	—	3.0	3.6	V
			Relative to $V_{DD\_HV\_IOx}$	$V_{DD\_HV\_IOx}$ – 0.1	$V_{DD\_HV\_IOx}$ + 0.1	
$V_{DD\_HV\_AD}$	SR	3.3 V ADC supply and high reference voltage	—	3.0	5.5	V
			Relative to $V_{DD\_HV\_REG}$	$V_{DD\_HV\_REG}$ – 0.1	5.5	
$V_{SS\_HV\_AD}$	SR	ADC ground and low reference voltage	—	0	0	V
$V_{DD\_LV\_REGCOR}$(3),(4)	SR	Internal supply voltage	—	—	—	V
$V_{SS\_LV\_REGCOR}$(3)	SR	Internal reference voltage	—	0	0	V
$V_{DD\_LV\_CORx}$(3),(4)	SR	Internal supply voltage	—	—	—	V
$V_{SS\_LV\_CORx}$(3)	SR	Internal reference voltage	—	0	0	V
T_A	SR	Ambient temperature under bias	—	–40	125	°C

1. Parametric figures can be out of specification when voltage drops below 4.5 V, however, guaranteeing the full functionality. In particular, ADC electrical characteristics and I/Os DC electrical specification may not be guaranteed.
2. The difference between each couple of voltage supplies must be less than 100 mV, $|V_{DD\_HV\_IOy} – V_{DD\_HV\_IOx}| < 100$ mV.
3. To be connected to emitter of external NPN. Low voltage supplies are not under user control—these are produced by an on-chip voltage regulator—but for the device to function properly the low voltage grounds ($V_{SS\_LV\_xxx}$) must be shorted to high voltage grounds ($V_{SS\_HV\_xxx}$) and the low voltage supply pins ($V_{DD\_LV\_xxx}$) must be connected to the external ballast emitter.
4. The low voltage supplies ($V_{DD\_LV\_xxx}$) are not all independent.
$V_{DD\_LV\_COR1}$ and $V_{DD\_LV\_COR2}$ are shorted internally via double bonding connections with lines that provide the low voltage supply to the data flash memory module. Similarly, $V_{SS\_LV\_COR1}$ and $V_{SS\_LV\_COR2}$ are internally shorted.
$V_{DD\_LV\_REGCOR}$ and $V_{DD\_LV\_REGCORx}$ are physically shorted internally, as are $V_{SS\_LV\_REGCOR}$ and $V_{SS\_LV\_CORx}$.

Figure 7 shows the constraints of the different power supplies.

Figure 8. Independent ADC supply



3.5 Thermal characteristics

Table 12. Thermal characteristics for 144-pin LQFP

Symbol		Parameter	Conditions	Typical value	Unit
$R_{\theta JA}$	D	Thermal resistance junction-to-ambient, natural convection(1)	Single layer board—1s	53.4	°C/W
	D		Four layer board—2s2p	43.9	°C/W
$R_{\theta JB}$	D	Thermal resistance junction-to-board(2)	Four layer board—2s2p	29.6	°C/W
$R_{\theta JCtop}$	D	Thermal resistance junction-to-case (top)(3)	Single layer board—1s	9.3	°C/W
Ψ_{JB}	D	Junction-to-board, natural convection(4)	Operating conditions	29.8	°C/W
Ψ_{JC}	D	Junction-to-case, natural convection(5)	Operating conditions	1.3	°C/W

1. Junction-to-ambient thermal resistance determined per JEDEC JESD51-7. Thermal test board meets JEDEC specification for this package.
2. Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.
3. Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.
4. Thermal characterization parameter indicating the temperature difference between the board and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.
5. Thermal characterization parameter indicating the temperature difference between the case and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JC.

Table 13. Thermal characteristics for 100-pin LQFP

Symbol		Parameter	Conditions	Typical value	Unit
$R_{\theta JA}$	D	Thermal resistance junction-to-ambient, natural convection(1)	Single layer board—1s	47.3	°C/W
	D		Four layer board—2s2p	35.6	°C/W
$R_{\theta JB}$	D	Thermal resistance junction-to-board(2)	Four layer board—2s2p	19.1	°C/W
$R_{\theta JCtop}$	D	Thermal resistance junction-to-case (top)(3)	Single layer board—1s	9.1	°C/W
Ψ_{JB}	D	Junction-to-board, natural convection(4)	Operating conditions	19.1	°C/W
Ψ_{JC}	D	Junction-to-case, natural convection(5)	Operating conditions	1.1	°C/W

1. Junction-to-ambient thermal resistance determined per JEDEC JESD51-7. Thermal test board meets JEDEC specification for this package.
2. Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.
3. Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.
4. Thermal characterization parameter indicating the temperature difference between the board and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.
5. Thermal characterization parameter indicating the temperature difference between the case and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JC.

3.5.1 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J, can be obtained from *Equation 1*:

Equation 1 $T_J = T_A + (R_{\theta JA} \times P_D)$

where:

T_A= ambient temperature for the package (^oC)

$R_{\theta JA}$= junction to ambient thermal resistance ($^oC/W$)

P_D= power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed in *Equation 2* as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

Equation 2 $R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$

where:

$R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)

$R_{\theta JC}$= junction to case thermal resistance (°C/W)

$R_{\theta CA}$= case to ambient thermal resistance (°C/W)

3.11 DC electrical characteristics

3.11.1 DC electrical characteristics (5 V)

Table 20 gives the DC electrical characteristics at 5 V (4.5 V < $V_{DD\_HV\_IOx}$ < 5.5 V, NVUSRO[PAD3V5V]=0) as described in *Figure 13*.

Figure 13. I/O input DC electrical characteristics definition

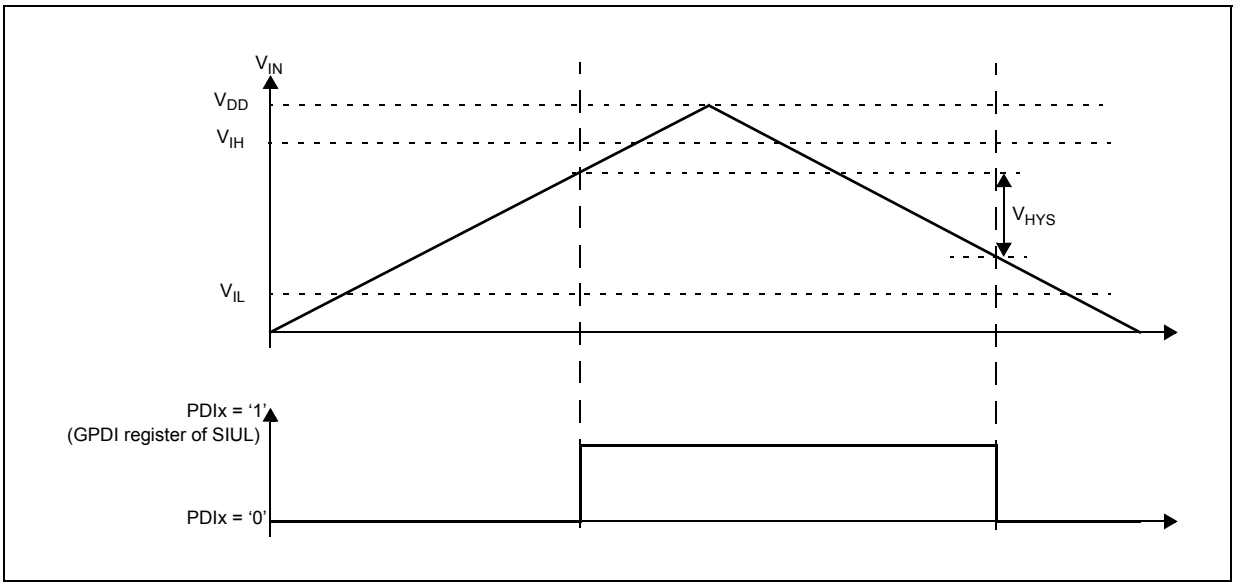


Table 20. DC electrical characteristics (5.0 V, NVUSRO[PAD3V5V]=0)

Symbol		Parameter	Conditions	Min	Max	Unit
V_{IL}	D	Minimum low level input voltage	—	–0.1(1)	—	V
V_{IL}	P	Maximum level input voltage	—	—	0.35 $V_{DD\_HV\_IOx}$	V
V_{IH}	P	Minimum high level input voltage	—	0.65 $V_{DD\_HV\_IOx}$	—	V
V_{IH}	D	Maximum high level input voltage	—	—	$V_{DD\_HV\_IOx}$ + 0.1(1)	V
V_{HYS}	T	Schmitt trigger hysteresis	—	0.1 $V_{DD\_HV\_IOx}$	—	V
V_{OL_S}	P	Slow, low level output voltage	I_{OL} = 3 mA	—	0.1 $V_{DD\_HV\_IOx}$	V
V_{OH_S}	P	Slow, high level output voltage	I_{OH} = –3 mA	0.8$V_{DD_HV_IOx}$	—	V
V_{OL_M}	P	Medium, low level output voltage	I_{OL} = 3 mA	—	0.1 $V_{DD\_HV\_IOx}$	V
V_{OH_M}	P	Medium, high level output voltage	I_{OH} = –3 mA	0.8 $V_{DD\_HV\_IOx}$	—	V
V_{OL_F}	P	Fast, low level output voltage	I_{OL} = 3 mA	—	0.1 $V_{DD\_HV\_IOx}$	V
V_{OH_F}	P	Fast, high level output voltage	I_{OH} = –3 mA	0.8 $V_{DD\_HV\_IOx}$	—	V
V_{OL_SYM}	P	Symmetric, low level output voltage	I_{OL} = 3 mA	—	0.1 $V_{DD\_HV\_IOx}$	V
V_{OH_SYM}	P	Symmetric, high level output voltage	I_{OH} = –3 mA	0.8 $V_{DD\_HV\_IOx}$	—	V

Table 20. DC electrical characteristics (5.0 V, NVUSRO[PAD3V5V]=0) (continued)

Symbol		Parameter	Conditions	Min	Max	Unit
I_{PU}	P	Equivalent pull-up current	$V_{IN} = V_{IL}$	–130	—	µA
			$V_{IN} = V_{IH}$	—	–10	
I_{PD}	P	Equivalent pull-down current	$V_{IN} = V_{IL}$	10	—	µA
			$V_{IN} = V_{IH}$	—	130	
I_{IL}	P	Input leakage current (all bidirectional ports)	T_A = –40 to 125 °C	–1	1	µA
I_{IL}	P	Input leakage current (all ADC input-only ports)	T_A = –40 to 125 °C	–0.5	0.5	µA
C_{IN}	D	Input capacitance	—	—	10	pF
I_{PU}	D	$\overline{\text{RESET}}$, equivalent pull-up current	$V_{IN} = V_{IL}$	–130	—	µA
			$V_{IN} = V_{IH}$	—	–10	
I_{PD}	D	$\overline{\text{RESET}}$, equivalent pull-down current	$V_{IN} = V_{IL}$	10	—	µA
			$V_{IN} = V_{IH}$	—	130	

1. “SR” parameter values must not exceed the absolute maximum ratings shown in *Table 9*.

Table 21. Supply current (5.0 V, NVUSRO[PAD3V5V]=0)

Symbol		Parameter		Conditions		Value		Unit
						Typ	Max	
$I_{DD\_LV\_CORE}$	T	Supply current	RUN — Maximum Mode(1)	$V_{DD\_LV\_CORE}$ externally forced at 1.3 V ADC Freq = 32 MHz PLL Freq = 64 MHz	64 MHz	90	120	mA
			RUN - Platform consumption, single core(2)	VDD_LV_CORE externally forced to 1.3V	16 MHz	21	37	
					40 MHz	35	55	
					64 MHz	48	72	
			RUN - Platform consumption, dual core(3)		16 MHz	24	41	
					40 MHz	42	64	
					64 MHz	58	85	
	P		RUN — Maximum Mode(4)	$V_{DD\_LV\_CORE}$ externally forced at 1.3 V	64 MHz	85	113	
			HALT Mode(5)	$V_{DD\_LV\_CORE}$ externally forced at 1.3 V	—	5.5	15	
			STOP Mode(6)	$V_{DD\_LV\_CORE}$ externally forced at 1.3 V	—	4.5	13	
I_{DD_FLASH}	T		Flash memory supply current during read	$V_{DD\_HV\_FL}$ at 5.0 V	—	—	14	
			Flash memory supply current during erase operation on 1 flash memory module	$V_{DD\_HV\_FL}$ at 5.0 V	—	—	42	
I_{DD_ADC}	T		ADC supply current — Maximum Mode	$V_{DD\_HV\_AD}$ at 5.0 V ADC Freq = 16 MHz	—	3	4	
I_{DD_OSC}	T		OSC supply current	V_{DD_OSC} at 5.0 V	8 MHz	2.6	3.2	

1. Maximum mode configuration: Code fetched from Flash executed by dual core, SIUL, PIT, ADC_0, eTimer_0/1, LINFlex_0/1, STM, INTC_0/1, DSPI_0/1/2/3/4, FlexCAN_0/1, FlexRay (static consumption), CRC_0/1, FCCU, SRAM enabled. I/O supply current excluded.
2. RAM, Code and Data Flash powered, code fetched from Flash executed by single core, all peripherals gated; IRC16MHz on, PLL64MHz OFF (except for code running at 64 MHz).
Code is performing continuous data transfer from Flash to RAM.
3. RAM, Code and Data Flash powered, code fetched from Flash executed by dual core, all peripherals gated; IRC16MHz on, PLL64MHz OFF (except for code running at 64 MHz).
Code is performing continuous data transfer from Flash to RAM.
4. Maximum mode configuration: Code fetched from RAM executed by dual core, SIUL, PIT, ADC_0, eTimer_0/1, LINFlex_0/1, STM, INTC_0/1, DSPI_0/1/2/3/4, FlexCAN_0/1, FlexRay (static consumption), CRC_0/1, FCCU, SRAM enabled. I/O supply current excluded.
5. HALT mode configuration, only for the “P” classification: Code Flash memory in low power mode, data Flash memory in power down mode, OSC/PLL are OFF, FIRC is ON, Core clock gated, all peripherals are disabled.
6. STOP mode configuration, only for the “P” classification: Code and data Flash memories in power down mode, OSC/PLL are OFF, FIRC is ON, Core clock gated, all peripherals are disabled.

Table 22. DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V]=1)(1) (continued)

Symbol		Parameter	Conditions	Min	Max	Unit
I_{PD}	P	Equivalent pull-down current	$V_{IN} = V_{IL}$	10	—	µA
			$V_{IN} = V_{IH}$	—	130	
I_{IL}	P	Input leakage current (all bidirectional ports)	T_A = –40 to 125 °C	—	1	µA
I_{IL}	P	Input leakage current (all ADC input-only ports)	T_A = –40 to 125 °C	—	0.5	µA
C_{IN}	D	Input capacitance	—	—	10	pF
I_{PU}	D	$\overline{\text{RESET}}$, equivalent pull-up current	$V_{IN} = V_{IL}$	–130	—	µA
			$V_{IN} = V_{IH}$	—	–10	
I_{PD}	D	$\overline{\text{RESET}}$, equivalent pull-down current	$V_{IN} = V_{IL}$	10	—	µA
			$V_{IN} = V_{IH}$	—	130	

1. These specifications are design targets and subject to change per device characterization.
2. “SR” parameter values must not exceed the absolute maximum ratings shown in *Table 9*.

Table 26. I/O consumption (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{RMSFST}	CC	D	Root medium square I/O current for FAST configuration	C_L = 25 pF, 40 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	22	mA
				C_L = 25 pF, 64 MHz		—	—	33	
				C_L = 100 pF, 40 MHz		—	—	56	
				C_L = 25 pF, 40 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	14	
				C_L = 25 pF, 64 MHz		—	—	20	
				C_L = 100 pF, 40 MHz		—	—	35	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		—	—	70	mA
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		—	—	65	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

3.12 Main oscillator electrical characteristics

The SPC56xP54x/SPC56xP60x provides an oscillator/resonator driver.

Table 27. Main oscillator electrical characteristics (5.0 V, NVUSRO[PAD3V5V]=0)

Symbol		Parameter	Min	Max	Unit
f_{OSC}	SR	Oscillator frequency	4	40	MHz
g_m	P	Transconductance	6.5	25	mA/V
V_{OSC}	T	Oscillation amplitude on EXTAL pin	1	—	V
t_{OSCSU}	T	Start-up time[1],[2]	8	—	ms

1. The start-up time is dependent upon crystal characteristics, board leakage, etc., high ESR and excessive capacitive loads can cause long start-up time.
2. Value captured when amplitude reaches 90% of EXTAL.

Table 28. Main oscillator electrical characteristics (3.3 V, NVUSRO[PAD3V5V]=1)

Symbol		Parameter	Min	Max	Unit
f_{OSC}	SR	Oscillator frequency	4	40	MHz
g_m	P	Transconductance	4	20	mA/V
V_{OSC}	T	Oscillation amplitude on EXTAL pin	1	—	V
t_{OSCSU}	T	Start-up time[1],[2]	8	—	ms

1. The start-up time is dependent upon crystal characteristics, board leakage, etc., high ESR and excessive capacitive loads can cause long start-up time.
2. Value captured when amplitude reaches 90% of EXTAL.

In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \times \frac{C_P \times C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

Equation 6

$$\tau_1 < (R_{SW} + R_{AD}) \times C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to *Equation 7*:

Equation 7

$$V_{A1} \times (C_S + C_{P1} + C_{P2}) = V_A \times (C_{P1} + C_{P2})$$

- A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Equation 8

$$\tau_2 < R_L \times (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S, a constraint on R_L sizing is obtained:

Equation 9

$$8.5 \times \tau_2 = 8.5 \times R_L \times (C_S + C_{P1} + C_{P2}) < T_S$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. *Equation 10* must be respected (charge balance assuming now C_S already charged at V_{A1}):

Equation 10

$$V_{A2} \times (C_S + C_{P1} + C_{P2} + C_F) = V_A \times C_F + V_{A1} \times (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the $R_F C_F$ filter, is not able to provide the extra charge to compensate the voltage drop on

3.15.2 ADC conversion characteristics

Table 32. ADC conversion characteristics

Symbol		Parameter	Conditions[1]	Value			Unit
				Min	Typ	Max	
V_{INAN}	SR	Analog input voltage[2]	—	$V_{SS\_HV\_AD}$ – 0.3	—	$V_{SS\_HV\_AD}$ + 0.3	V
f_{CK}	SR	ADC Clock frequency (depends on ADC configuration) (The duty cycle depends on AD_clk[3] frequency)	—	3[4]	—	60	MHz
f_s	SR	Sampling frequency	—	—	—	1.53	MHz
t_{ADC_S}	D	Sample time[5]	f_{ADC} = 20 MHz, INPSAMP = 3	125	—	—	ns
			f_{ADC} = 9 MHz, INPSAMP = 255	—	—	28.2	µs
t_{ADC_C}	P	Conversion time[6]	f_{ADC} = 20 MHz[7], INPCMP = 1	0.650	—	—	µs
C_S[8]	D	ADC input sampling capacitance	—	—	—	2.5	pF
C_{P1}[8]	D	ADC input pin capacitance 1	—	—	—	3	pF
C_{P2}[8]	D	ADC input pin capacitance 2	—	—	—	1	pF
C_{P3}[8]	D	ADC input pin capacitance 3	—	—	—	1	pF
R_{SW1}[8]	D	Internal resistance of analog source	$V_{DD\_HV\_AD}$ = 5 V ±10%	—	—	0.6	kΩ
			$V_{DD\_HV\_AD}$ = 3.3 V ±10%	—	—	3	kΩ
R_{SW2}[8]	D	Internal resistance of analog source	$V_{DD\_HV\_AD}$ = 5 V ±10%	—	—	2.15	kΩ
			$V_{DD\_HV\_AD}$ = 3.3 V ±10%	—	—	3.6	kΩ
R_{AD}[8]	D	Internal resistance of analog source	—	—	—	2	kΩ
I_{INJ}	T	Input current injection	Current injection on one ADC input, different from the converted one. Remains within TUE spec.	–5	—	5	mA
INL	P	Integral Non Linearity	No overload	—	±1.5	—	LSB
DNL	P	Differential Non Linearity	No overload	–1.0	—	1.0	LSB
OFS	T	Offset error	—	—	±1	—	LSB
GNE	T	Gain error	—	—	±1	—	LSB
TUE	P	Total unadjusted error without current injection	16 precision channels	–2.5	—	2.5	LSB

Table 37. $\overline{\text{RESET}}$ electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	$V_{DD}+0.4$	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	—	–0.4	—	$0.35V_{DD}$	V
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	V
V_{OL}	CC	P	Output low level	Push Pull, I_{OL} = 2mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
				Push Pull, I_{OL} = 1mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	—	—	$0.1V_{DD}$	
				Push Pull, I_{OL} = 1mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	
T_{tr}	CC	D	Output transition time output pin[3] MEDIUM configuration	C_L = 25pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	10	ns
				C_L = 50pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	
				C_L = 100pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	40	
				C_L = 25pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	12	
				C_L = 50pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	25	
				C_L = 100pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
W_{FRST}	SR	P	$\overline{\text{RESET}}$ input filtered pulse	—	—	—	40	ns
W_{NFRST}	SR	P	$\overline{\text{RESET}}$ input not filtered pulse	—	500	—	—	ns
T_{POR}	CC	D	maximum delay before internal reset is released after all VDD_HV reach nominal supply	Monotonic VDD_HV supply ramp	—	—	1	ms
$\lvert I_{WPU}\rvert$	CC	P	Weak pull-up current absolute value	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	10	—	150	µA
				V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	10	—	150	
				V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[4]	10	—	250	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 °C to $T_{A\ MAX}$, unless otherwise specified.
2. This is a transient configuration during power-up, up to the end of reset PHASE2 (refer to RGM module section of device reference manual).
3. C_L includes device and package capacitance (C_{PKG} < 5 pF).
4. The configuration PAD3V5 = 1 when V_{DD} = 5 V is only transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 44. Document revision history (continued)

Date	Revision	Substantive changes
21-Nov-2012	4	In the cover page, replaced “64 MHz, dual issue, 32-bit CPU core complex” with “64 MHz, single issue, 32-bit CPU core complex” *Table 9: Absolute maximum ratings*, updated TV_{DD} entry *Table 22: DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V]=1)*: Updated conditions value of V_{OL_F} to 11 mA Updated conditions value of V_{OH_F} to – 11 mA *Table 24: Peripherals supply current (5 V and 3.3 V)*: Replaced all occurrences of I_{DD_BV} in this table with I_{DD_HV} Replaced all occurrences of VDD_BV in this table with VDD_HV_REG. *Figure 40: Ordering information scheme*, fixed typo in the footnote.
18-Sep-2013	5	Updated Disclaimer.
15-Jun-2016	6	Added “AEC-Q10x qualified” in *Features* section. In *Table 2: SPC56xP54x/SPC56xP60x device comparison* added footnote “LinFlex_1 is Master Only.” related to row “LINFlex modules” Updated *Table 3: SPC56xP54x/SPC56xP60x device configuration difference* *Figure 2: LQFP176 pinout (top view)*: – Changed PB[4] to TDO – Changed PB[5] to TDI – Changed pins 71,72 to NC – Changed pins 87,88 to NC In *Section 1.5.27: Nexus development interface (NDI)*, added note “At least one TCK clock is necessary for the EVTI signal to be recognized by the MCU.” for EVTI pin. In *Table 7: Pin muxing*: – Replaced “PCR register” with “PCR No.” – Updated “CS3” with “CS3_4” function related to A[2] port pin – In column “I/O direction”, added “O” for “DSPI_1” peripheral – In “Functions” column related to D[12] port pin, changed DS7_1 to CS7_1